

# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	100	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	T <sub>C</sub> = +25°C T <sub>C</sub> = +70°C	۱ <sub>D</sub>	17 13	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	IDM	20	A	
Avalanche Current, L = 1mH		I <sub>AS</sub>	7.5	A
Avalanche Energy, L = 1mH		E <sub>AS</sub>	28.5	mJ

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Dower Discipation (Note 5)	T <sub>C</sub> = +25°C	D	34	W
Total Power Dissipation (Note 5)	T <sub>C</sub> = +70°C	P <sub>D</sub>	22	
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	51	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R <sub>0JC</sub>	3.6	C/W	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.5	2	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	n	_	67	80		V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.3A	
	R <sub>DS (ON)</sub>	_	69	99	mΩ	V <sub>GS</sub> = 6V, I <sub>D</sub> = 3A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.77	_	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 3.2A	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C <sub>iss</sub>		1172	—		V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	C <sub>oss</sub>	_	40.8	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	31.3	_			
Gate Resistance	R <sub>G</sub>	_	1.6	—	Ω	$V_{DS}$ = 0V, $V_{GS}$ = 0V, f = 1MHz	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	25.2	—			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	12.2	_	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 3.3A	
Gate-Source Charge	Q <sub>gs</sub>	_	5.3	_	IIC IIC		
Gate-Drain Charge	Q <sub>gd</sub>	_	5.9	_			
Turn-On Delay Time	t <sub>D(on)</sub>		5.4	_			
Turn-On Rise Time	tr		5.9	_		$V_{DD}$ = 50V, $R_{G}$ = 6.0 $\Omega$ , $I_{D}$ = 3.3A	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	20	_	ns		
Turn-Off Fall Time	t <sub>f</sub>	_	7.3	—	1		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	_	19.7	—	ns		
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	_	15.9	_	nC	-I <sub>F</sub> = 3.3A, dI/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. 6. Guaranteed by design. Not subject to product testing.

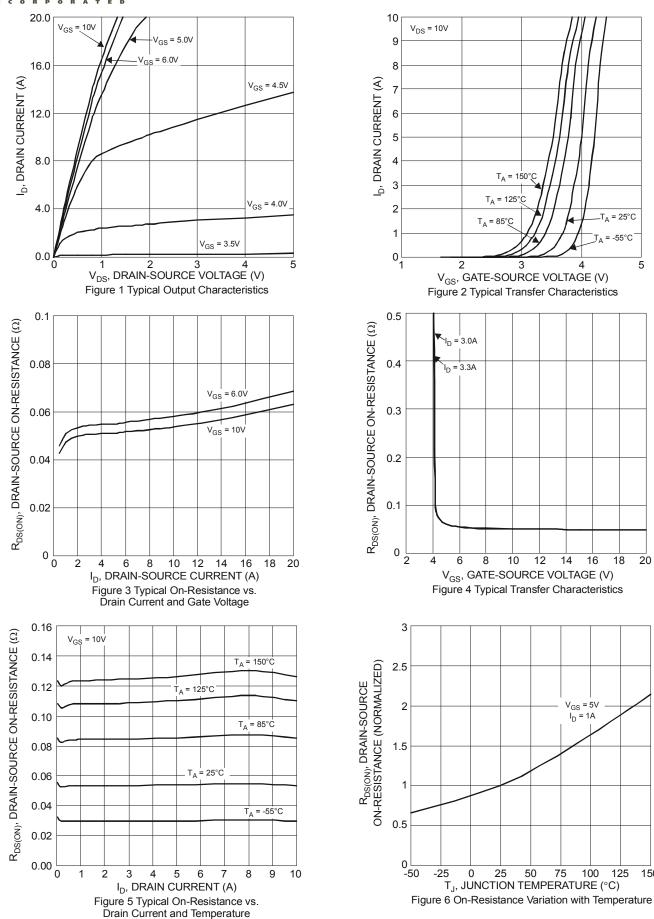
Guaranteed by design. Not subject to product testing.
Short duration pulse test used to minimize self-heating effect.



## DMN10H099SK3

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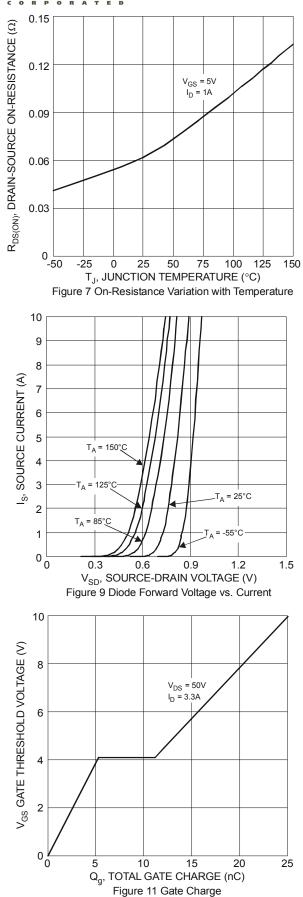


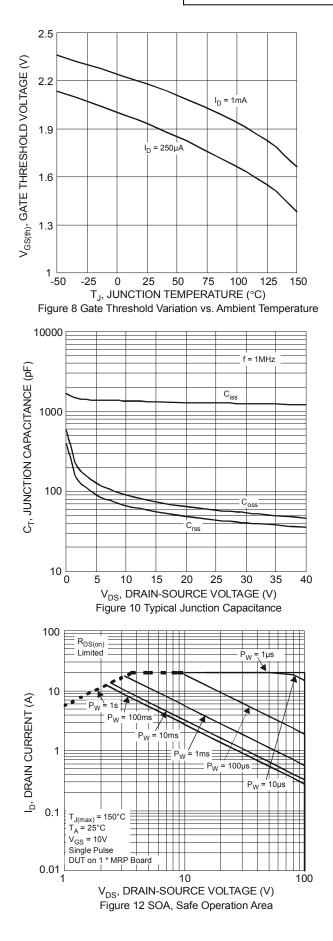
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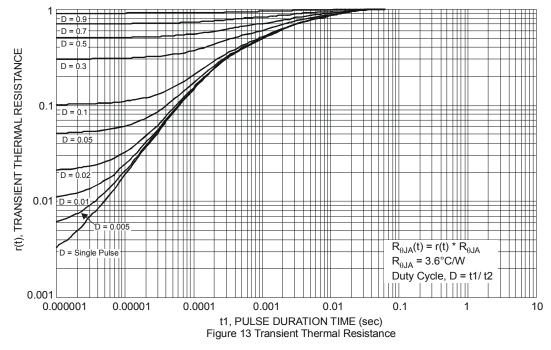




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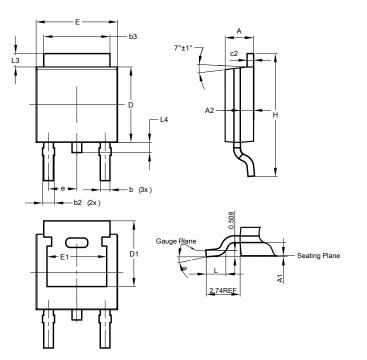


**NEW PRODUCT** 



## Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.

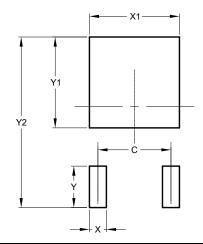


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
c2	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Ε	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					



## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Y	2.600			
Y1	5.700			
Y2	10.700			

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